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Description

The ATBTLC1000-MR110CA is an ultra-low power Bluetooth® SMART (BLE 4.1) module with Integrated Transceiver, Modem, MAC, PA, TR Switch, and Power Management Unit (PMU). It can be used as a Bluetooth Low Energy link controller or data pump with external host MCU.

The qualified Bluetooth® Smart protocol stack is stored in dedicated ROM, the firmware includes L2CAP service layer protocols, Security Manager, Attribute protocol (ATT), Generic Attribute Profile (GATT), and the Generic Access Profile (GAP). Additionally, application profiles such as Proximity, Thermometer, Heart Rate, Blood Pressure and many others are supported and included in the protocol stack.

The module contains all circuitry required including a ceramic high gain antenna, 26MHz crystal, and PMU circuitry. The customer simply needs to place the module on his board and provide power and a 32kHz Real Time Clock or crystal.

Features

- Complies with Bluetooth V4.1, ETSI EN 300 328, and EN 300 440 Class 2, FCC CFR47 Part 15, ARIB STD-T66, and TELEC
- Bluetooth Certification
 - QD ID Controller (see declaration D028678)
 - QD ID Host (see declaration D028679)
- 2.4GHz transceiver and Modem
 - -95dBm/-93dBm programmable receiver sensitivity
 - -20 to +3.5dBm programmable TX output power
 - Integrated T/R switch
 - Single wire antenna connection
- ARM Cortex®-M0 32-bit processor
 - Single wire Debug (SWD) interface
 - 4-channel DMA controller
 - Brown out detector and Power On Reset
 - Watch Dog Timer
- Memory
 - 128kB embedded RAM (96kB available for application)
 - 128kB embedded ROM
- Hardware Security Accelerators
 - AES-128
 - SHA-256

- Peripherals
 - 12 digital and 1 wakeup GPIO
 - Two Mixed Signal GPIOs
 - Programmable 96kΩ pull-up or pull-down resistor for each GPIO
 - Retention capable GPIO pads
 - 1x SPI (Master/Slave)
 - 2x I²C (Master/Slave)
 - 2x UART
 - 1x SPI Flash
 - 3-axis quadrature decoder
 - 4x Pulse Width Modulation (PWM), three General Purpose Timers, and one Wakeup Timer
 - 2-channel 11-bit ADC
- Clock
 - Integrated 26MHz oscillator
 - 26MHz crystal oscillator
 - Fully integrated sleep oscillator
 - 32kHz RTC crystal oscillator
- Ultra Low power
 - Less than 1.15μA (8KB RAM retention and RTC running)
 - 3.0mA peak TX current (VBAT=3.6V, 0dBm TX power)
 - 4.2mA peak RX current (VBAT=3.6V, -95dBm sensitivity)
 - Very low average advertisement current (dependent on advertisement interval)
- Integrated Power management
 - 1.8-4.3V input range for PMU
 - 1.62-4.3V input range for I/O
 - Fully integrated Buck DC-DC converter

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1 Ordering Information

Table 1-1. Ordering code

Ordering code	Package	Description
ATBTLC1000-MR110CA	12.7 X 20.15mm	Chip Antenna

2 Package Information

Table 2-1. ATBTLC1000-MR110CA Module Information ⁽¹⁾

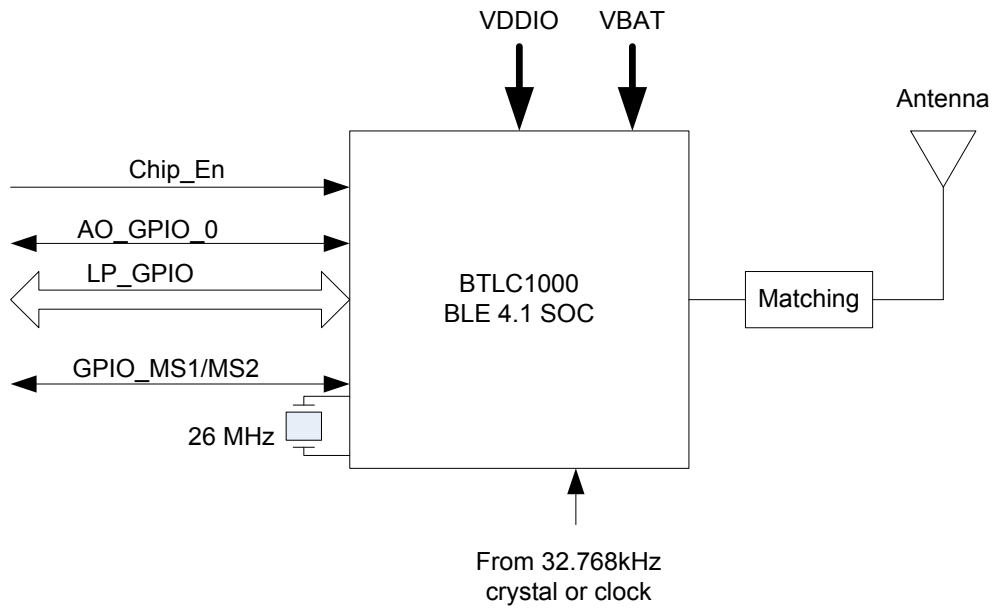
Parameter	Value	Units	Tolerance
Package Size	12.700 X 20.152	mm	
Pad Count	24		
Total Thickness	2.0874	mm	±0.078
Pad Pitch	0.9002		
Pad Width	0.600		
Exposed Paddle Pad size	2.7 x 2.7		

Note: 1. For details, see Package Drawing in Section 4.3.

3 Block Diagram

Figure 3-1 shows the block diagram of the ATBTLC1000-MR110CA module.

Figure 3-1. Block Diagram

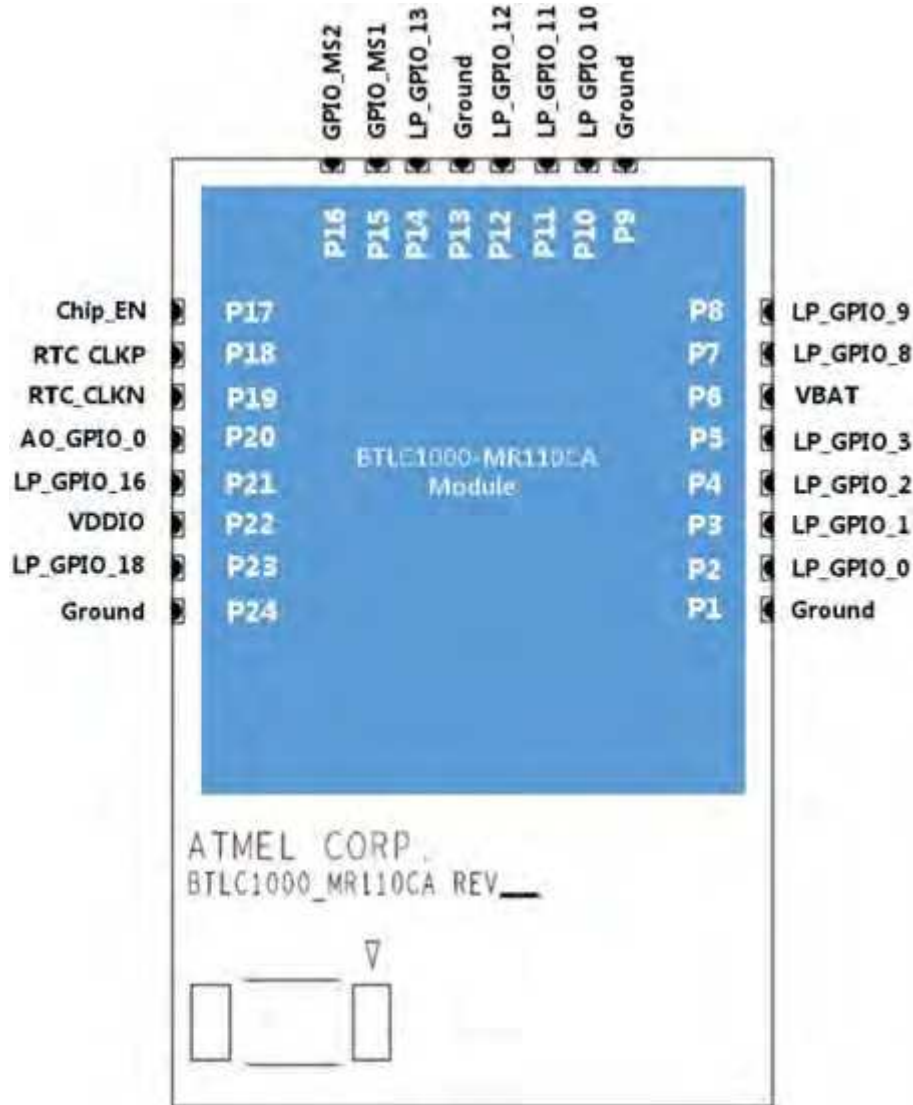


4 Pinout Information

4.1 Pin Assignment

Figure 4-1 shows the module top view and pin numbering.

Figure 4-1. ATBTLC1000 Pin Descriptions



4.2 Pin Description

Table 4-1 provides details for the module pin assignments and descriptions.

Table 4-1. Pin Description

NO	Name	Type	Description	Notes
1	Ground	Power	Ground Pin. Connect to PCB ground.	
2	LP_GPIO_0	I/O	Used for Single Wire Debug Clock	Debug interface pin. Connect to a header or test point.
3	LP_GPIO_1	I/O	Used for Single Wire Debug Data	Debug interface pin. Connect to a header or test point
4	LP_GPIO_2	I/O	General Purpose I/O	Default function is Host UART RxD
5	LP_GPIO_3	I/O	General Purpose I/O	Default function is Host UART TxD
6	VBAT	Power	Power Supply Pin for the on chip Power Management Unit (PMU). Connect to a 1.8V – 4.3V power supply.	
7	LP_GPIO_8	I/O	General Purpose I/O	Default function is Host UART CTS
8	LP_GPIO_9	I/O	General Purpose I/O	Default function is Host UART RTS
9	Ground	Power	Ground Pin. Connect to PCB ground.	
10	LP_GPIO_10	I/O	General Purpose I/O	Default function is SPI_SCK
11	LP_GPIO_11	I/O	General Purpose I/O	Default function is SPI_MOSI
12	LP_GPIO_12	I/O	General Purpose I/O	Default function is SPI_SSN
13	Ground	Power	Ground Pin. Connect to PCB ground.	
14	LP_GPIO_13	I/O	General Purpose I/O	Default function is SPI_MISO
15	GPIO_MS1	I/O	Mixed Signal I/O	Configurable to be a GPIO or ADC input
16	GPIO_MS2	I/O	Mixed Signal I/O	Configurable to be a GPIO or ADC input
17	Chip_En	Control	Chip Enable. A high level turns on the On Chip PMU and enables operation of the device. Low disables the device and turns off the PMU.	Control this pin with a host GPIO. If not used, tie to VDDIO.
18	RTC_CLKP		Positive Pin for Real Time Clock Crystal	Connect to a 32.768kHz Crystal
19	RTC_CLKN		Negative Pin for Real Time Clock Crystal	Connect to a 32.768kHz Crystal
20	AO_GPIO_0	I/O	Always on GPIO_0. Used to wake up the device from sleep.	
21	LP_GPIO_16	I/O	General Purpose I/O	Default function is Debug UART RxD
22	VDDIO	Power	Power Supply Pin for the I/O pins. Connect to a 1.62V – 4.3V power supply.	I/O supply can be less than or equal to VBAT
23	LP_GPIO_18	I/O	General Purpose I/O.	Default function is Debug UART TxD
24	Ground	Power	Ground Pin. Connect to PCB ground	
25	Paddle	Power	Center Ground Paddle	Connect to inner PCB ground plane with an array of vias

4.3 Module Outline Drawing

Figure 4-2 shows the view of the module and the module dimensions. All dimensions are in mm.

Figure 4-2. Module Dimensions (millimeters)

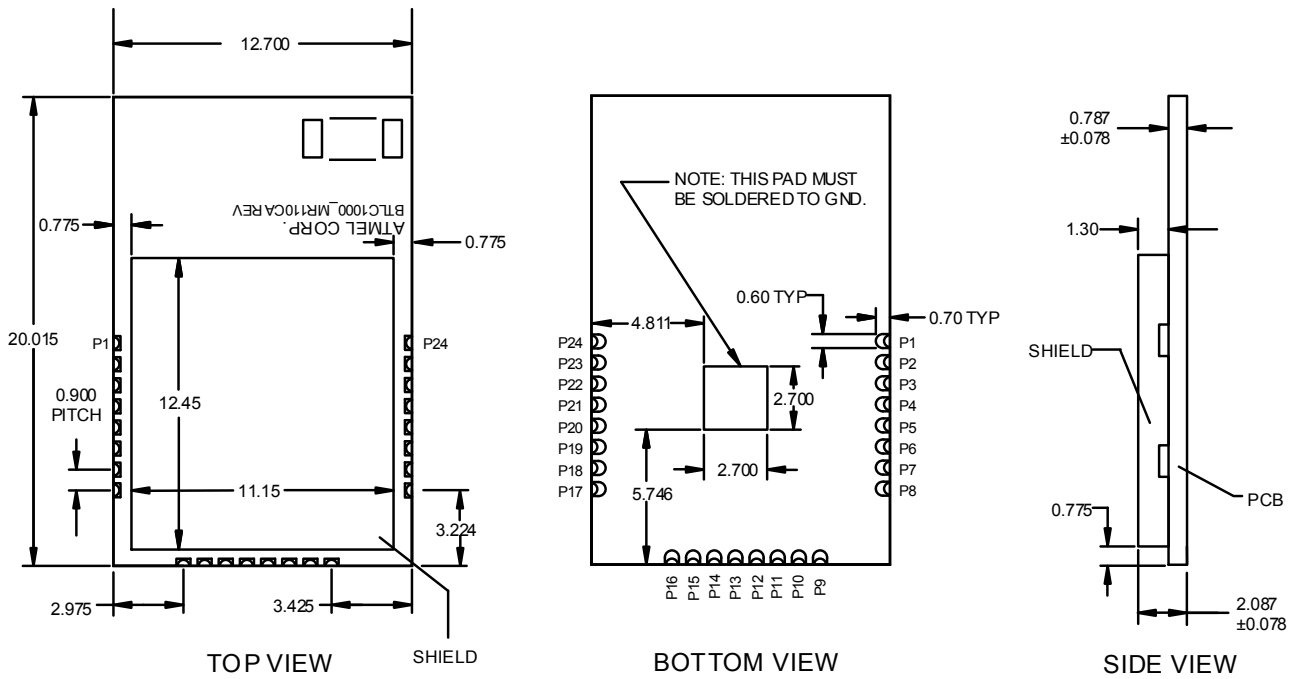
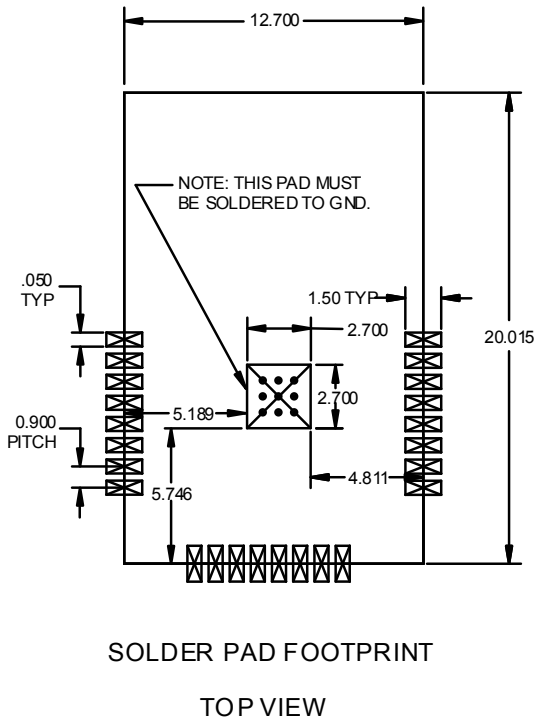


Figure 4-3. Customer PCB Footprint



5 Electrical Specifications

5.1 Absolute Maximum Ratings

This section describes the minimum and maximum ratings the module can tolerate.

Table 5-1. ATBTLC1000-MR110CA Absolute Maximum Ratings

Symbol	Characteristics	Min.	Max.	Unit
VDDIO	I/O Supply Voltage	-0.3	5.0	V
VBAT	Battery Supply Voltage	-0.3	5.0	V
VIN ⁽¹⁾	Digital Input Voltage	-0.3	VDDIO	V
VAIN ⁽²⁾	Analog Input Voltage	-0.3	1.5	V
VESDHBM ⁽³⁾	ESD Human Body Model	-1000, -2000 (see notes below)	+1000, +2000 (see notes below)	V
TA	Storage Temperature	-65	150	°C
	Junction Temperature		125	°C

- Notes:
- VIN corresponds to all the digital pins.
 - VAIN corresponds to the following analog pins: VDDRF_RX, VDDAMS, RFIO, RTC_CLKN, RTC_CLKP, VDD_SXDIG, VDD_VCO.
 - For VESDHBM, each pin is classified as Class 1, or Class 2, or both:
 - The Class 1 pins include all the pins (both analog and digital)
 - The Class 2 pins include all digital pins only
 - VESDHBM is ± 1 kV for Class1 pins. VESDHBM is ± 2 kV for Class2 pins.

5.2 Recommended Operating Conditions

Table 5-2. ATBTLC1000-MR110CA Recommended Operating Conditions

Symbol	Characteristics	Min.	Typ.	Max.	Unit
VDDIO	I/O Supply Voltage Low Range	1.62	1.80	4.3	V
VBAT	Battery Supply Voltage	1.8 ⁽¹⁾	3.6	4.3	V
	Operating Temperature	-40		85	°C

- Note:
- VBAT supply must be greater than or equal to VDDIO.

5.3 Restrictions for the Power States

When VDDIO is off (either disconnected or at ground potential), a voltage must not be applied to the device pins. This is because each pin contains an ESD diode from the pin to the VDDIO supply. This diode will turn ON when a voltage higher than one diode-drop is supplied to the pin. This, in turn, will try to power up the part through the VDDIO supply.

If a voltage must be applied to the signal pads while the chip is in a low power state, the VDDIO supply must be on.

Similarly, to prevent the pin-to-ground diode from turning on, do not apply a voltage that is more than 0.3V below ground to any pin.

5.4 Power Sequences

Describes that sequence and parameters for powering up and down the device.

5.4.1 Power-up Sequence

The power-up sequence for ATBTLC1000 is shown in [Figure 5-1](#). The timing parameters are provided in [Table 5-3](#).

Figure 5-1. ATBTLC1000 Power-up Sequence

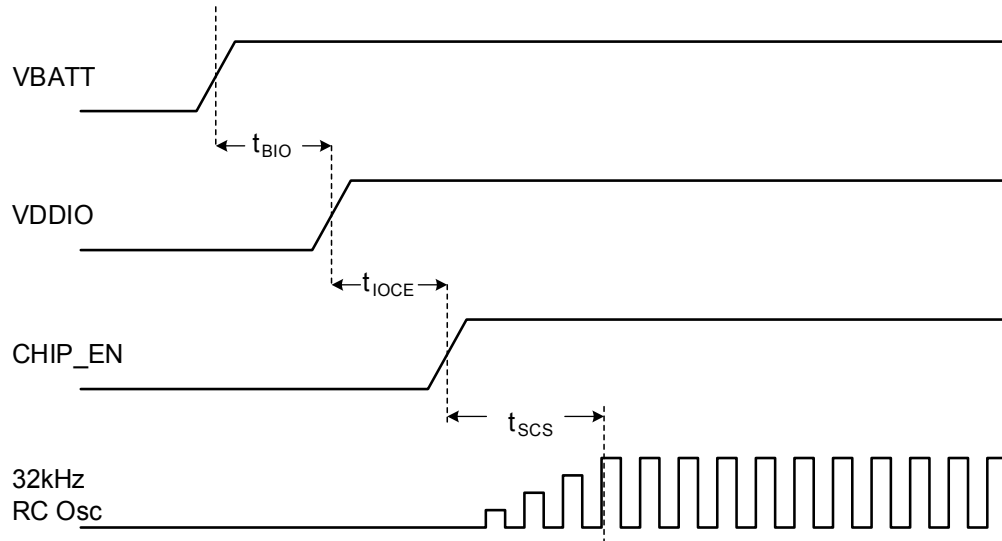


Table 5-3. ATBTLC1000 Power-up Sequence Timing

Parameter	Min.	Max.	Unit	Description	Notes
t_{BIO}	0		Ms	VBAT rise to VDDIO rise	VBAT and VDDIO can rise simultaneously or can be tied together.
t_{IOCE}	0			VDDIO rise to CHIP_EN rise	CHIP_EN must not rise before VDDIO. CHIP_EN must be driven high or low, not left floating.
t_{SCS}	10		μ s	CHIP_EN rise to 31.25kHz (2MHz/64) oscillator stabilizing	

5.4.2 Power-down Sequence

The power-down sequence for ATBTLC1000 is shown in Figure 5-2. The timing parameters are provided in Table 5-5.

Figure 5-2. ATBTLC1000 Power-down Sequence

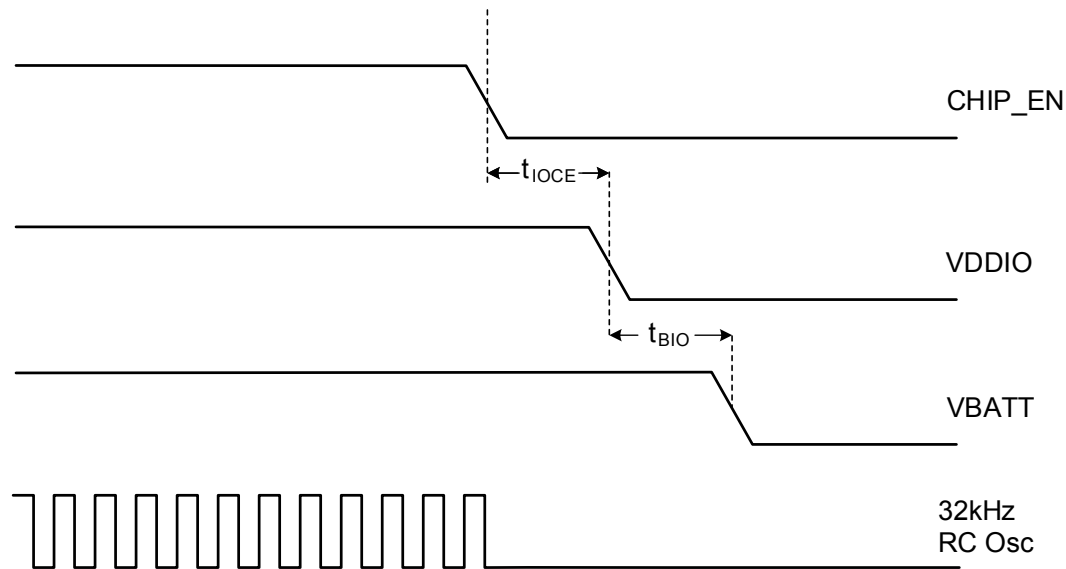


Table 5-4. ATBTLC1000 Power-down Sequence Timing

Parameter	Min.	Max.	Unit	Description	Notes
t_{IOCE}	0		ms	CHIP_EN fall to VDDIO fall	CHIP_EN must fall before VDDIO. CHIP_EN must be driven high or low, not left floating
t_{BIO}	0			VDDIO fall to VBAT fall	VBAT and VDDIO can fall simultaneously or can be tied together

5.5 Digital I/O Pin Behavior During Power-up Sequences

Table 5-5 describes the digital I/O Pin states corresponding to device power modes.

Table 5-5. Digital I/O Pin Behavior in the Different Device States

Device state	VDDIO	CHIP_EN	RESETN	Output driver	Input driver	Pull-up/down resistor (96k Ω)
Power_Down: core supply off	High	Low	Low	Disabled (Hi-Z)	Disabled	Disabled
Power-On Reset: core supply on	High	High	Low	Disabled (Hi-Z)	Disabled	Enabled
Power-On Default: core supply on, device out of reset but not programmed yet	High	High	High	Disabled (Hi-Z)	Enabled	Enabled
Power-On Default: core supply on, device out of reset but not programmed yet	High	High	High	Programmed by firmware for each pin: Enabled or Disabled	Opposite of Output Driver state	Programmed by firmware for each pin: Enabled or Disabled

5.6 RTC Pins

Module pins 18 and 19 (RTC_CLKP and RTC_CLKN, respectively) are used for a 32.768kHz crystal. To be compliant with the BLE specifications for connection events, the frequency accuracy of this clock has to be within ± 500 ppm. Because of the low drift of the 32.768kHz crystal oscillator clock and the fact that it can be accurately calibrated (± 25 ppm), the power consumption of the ATBTLC1000 can be minimized by leaving radio circuits in low power sleep mode for as long as possible until they need to wake up for the next connection timed event.

The block diagram in [Figure 5-3\(a\)](#) shows how the internal low-frequency Crystal Oscillator (XO) is connected to the external crystal.

Typically, the crystal should be chosen to have a load capacitance of 7pF to minimize the oscillator current.

Alternatively, if an external 32.768kHz clock is available, it can be used to drive the RTC_CLKP pin instead of using a crystal. The XO has 6pF internal capacitance on the RTC_CLKP pin. To bypass the crystal oscillator an external signal capable of driving 6pF can be applied to the RTC_CLK_P terminal as shown in [Figure 5-3\(b\)](#). This signal must be 1.2V maximum. RTC_CLK_N must be left unconnected when driving an external source into RTC_CLK_P.

Figure 5-3. ATBTLC1000 Connections to Low-Frequency Crystal Oscillator

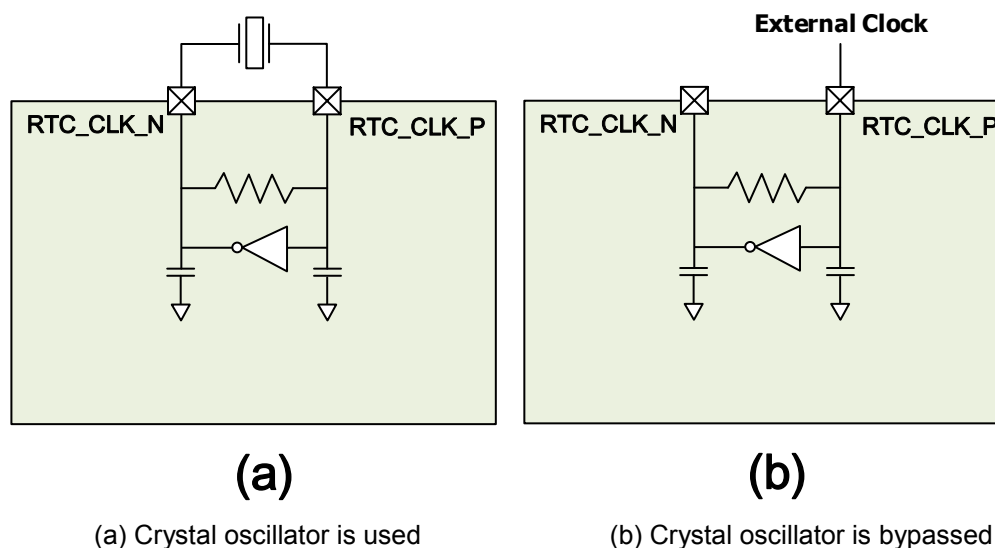


Table 5-6. ATBTLC1000-MR110CA 32.768kHz External Clock Specification

Parameter	Min.	Typ.	Max	Unit	Comments
Oscillation frequency		32.768		kHz	Must be able to drive 6pF load @ desired frequency
VinH	0.7		1.2	V	High level input voltage
VinL	0		0.2	V	Low level input voltage
Stability – Temperature	-250		+250	ppm	

6 Characteristics

6.1 Device States

Table 6-1. ATBTLC1000-MR110CA Device States

Device state	CHIP_EN	VDDIO	I _{VBAT} (typical)	I _{VDDIO} (typical)	Remarks
BLE_On_Transmit	On	On	3.0mA	12μA	VBAT = 3.6V @ 0dBm Pout
BLE_On_Receive	On	On	4.5mA	12μA	VBAT = 3.6V
Ultra Low Power	On	On	1.25μA	0.2μA	With 8KB retention memory, BLE Timer and RTC enabled
Power_Down	GND	On	<0.05μA	<0.05μA	Chip Enable Off

6.2 Receiver Performance

Table 6-2. ATBTLC1000-MR110CA Receiver Performance

Parameter	Min.	Typ.	Max.	Unit
Frequency	2,402		2,480	MHz
Sensitivity with on-chip DC/DC	94.5	-93		dBm
Maximum Receive Signal Level		5		dBm
CCI		13		dB
ACI (N±1)		0		dB
N+2 Blocker (Image)		-20		dB
N-2 Blocker		-38		dB
N+3 Blocker (Adj. Image)		-35		dB
N-3 Blocker		-43		dB
N±4 or greater		-45		dB
Intermod (N+3, N+6)		-33		dBm
OOB (2GHz<f<2.399GHz)	-15			dBm
OOB (f<2GHz)	-10			dBm

All measurements performed at 3.6V VBAT and 25°C, with tests following Bluetooth V4.1 standard tests.

6.3 Transmitter Performance

Table 6-3. ATBTLC1000-MR110CA Transmitter Performance

Parameter	Min.	Typ.	Max.	Unit
Frequency	2,402		2,480	MHz
Output Power Range	-20		3.5	dBm
Minimum Output Power	-55			
In-band Spurious (N±2)		-40		dBm
In-band Spurious (N±3)		-50		dBm
2nd Harmonic Pout		-45		dBm
Frequency Dev		±250		kHz

All measurements performed at 3.6V VBAT and 25°C, with tests following Bluetooth V4.1 standard tests.

7 Schematic Content

This chapter provides the schematic data for the ATBTLC1000 chip functionality on the ATBTLC1000-MR210 module. Module design information such as module schematics can be obtained under an NDA from Atmel.

7.1 Application Schematic

The ATBTLC1000-MR110CA module is fully self-contained. To use the module, just provide VBAT and VDDIO supplies. [Figure 7-1](#) shows a typical design using the ATBTLC1000-MR110CA module. The schematic shows several host interfaces: UART with Flow Control (4-wire) and SPI as well as an input to the ADC on the GPIO_MS2 pin. A user can choose the interface(s) required for their application. If a 32.768kHz Real Time Clock is not available in the system, a 32.768kHz crystal can be used. [Figure 7-2](#) shows a design using a crystal for the Real Time Clock. The crystal should be specified with a load capacitance, $CL=7pF$ and a total frequency error of 200ppm.

Figure 7-1. Application Schematic Including 32.768kHz Crystal

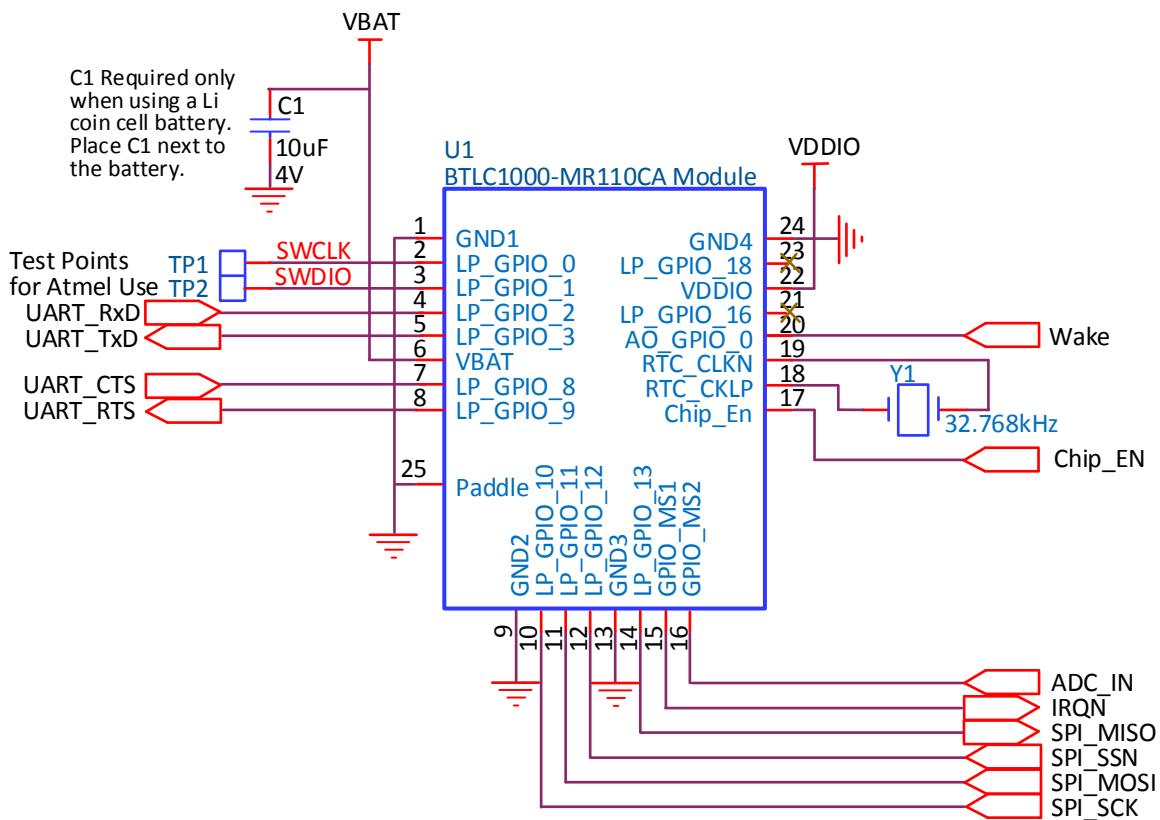
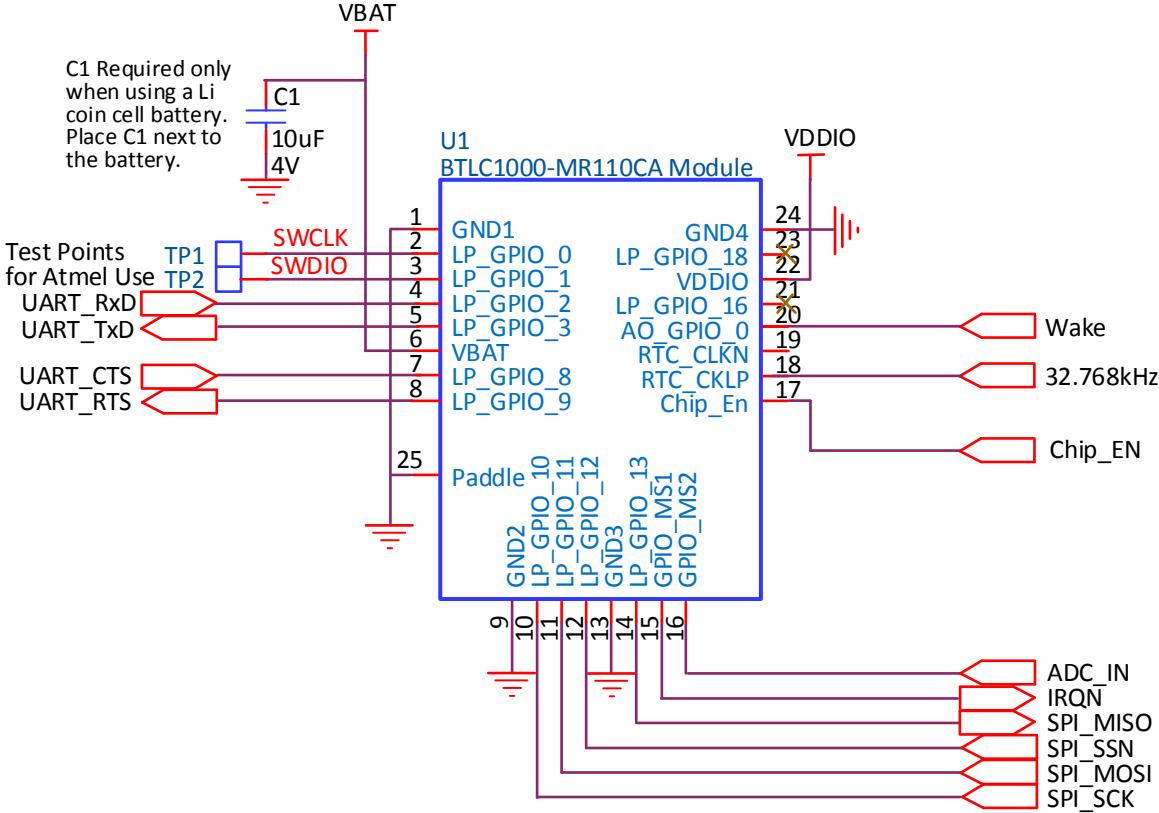


Figure 7-2. Application Schematic without 32.768kHz Crystal



8 Placement and Routing Guidelines

It is critical to follow the recommendations listed below to achieve the best RF performance:

1. The board should have a solid ground plane. The center ground pad of the device must be soldered to the ground plane by using a 3 x 3 grid of vias (see [Figure 4-3](#)). Each ground pin of the ATBTLC1000-MR110CA should have a ground via placed either in the pad or right next to the pad going down to the ground plane.
2. When the module is placed on the customer PCB design, a provision for the antenna must be made. There should be nothing under the portion of the module, which contains the antenna. This means the antenna should not be placed directly on top of the customer PCB as shown in [Figure 8-1 \(a\)](#). This can be accomplished by, for example, placing the module at the edge of the board such that the module edge with the antenna extends beyond the customer PCB edge by 6.5mm as shown in [Figure 8-1 \(b\)](#). Alternatively, a cutout in the customer PCB can be provided under the antenna. The cutout should be at least 22mm x 6.5mm (see [Figure 8-1 \(c\)](#) and [Figure 8-2](#)). If the cutout method is used, the ATBTLC1000-MR110CA should be centered in the cutout. The ATBTLC1000-MR110CA must have ground vias spaced 2.5mm apart that should be placed all around the perimeter of the cutout. No large components should be placed near the antenna.
3. Keep away from antenna, as far as possible, large metal objects to avoid electromagnetic field blocking
4. Do not enclose the antenna within a metal shield
5. Keep any components that may radiate noise or signals within the 2.4GHz – 2.5GHz frequency band far away from the antenna or better yet, shield the components that are generating the noise. Any noise radiated from the customer PCB in this frequency band will degrade the sensitivity of the ATBTLC1000-MR110CA module.

Figure 8-1. ATBTLC1000-MR110CA Placement Reference

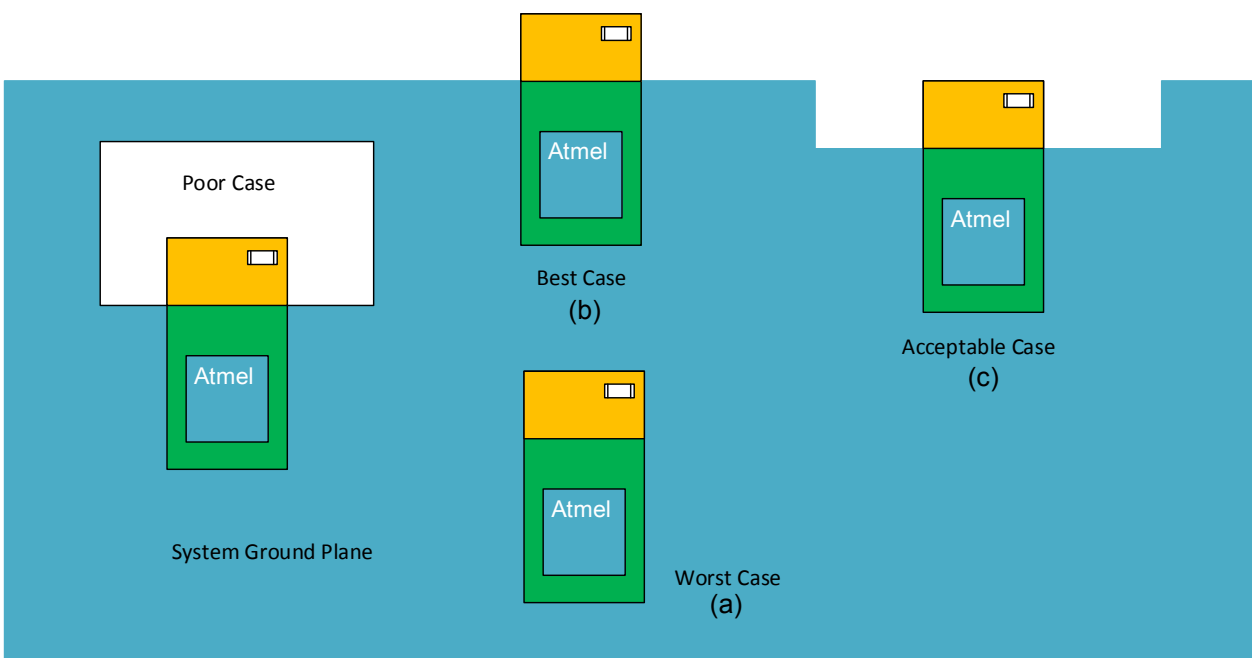
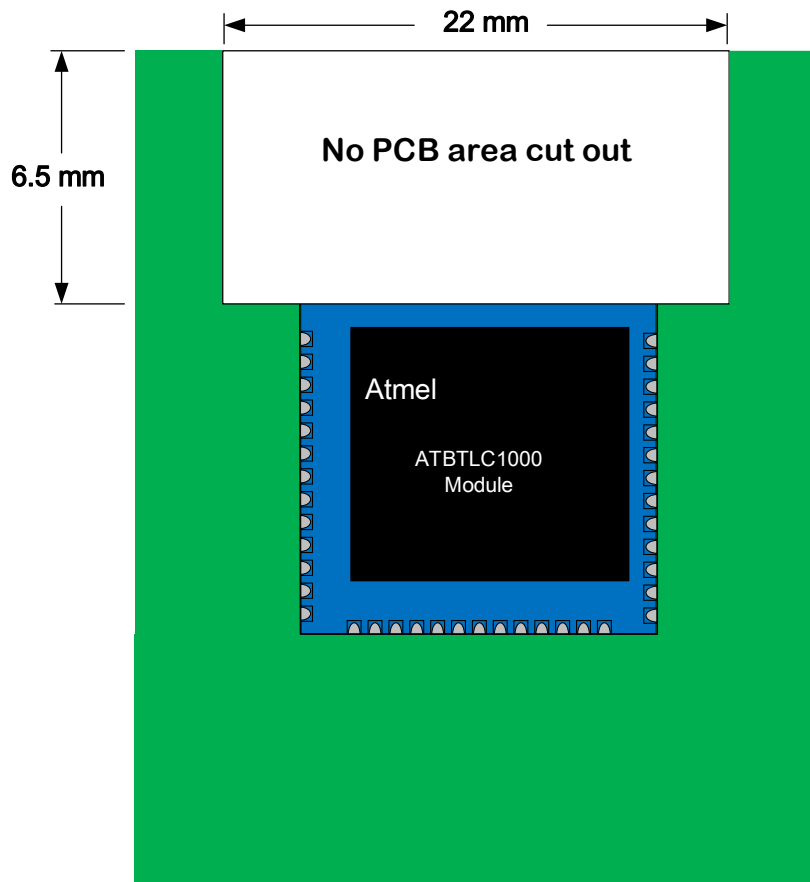


Figure 8-2. No PCB/GND Cut Out Area



8.2 Power and Ground

Dedicate one layer as a ground plane. Make sure that this ground plane does not get broken up by routes. Power can route on all layers except the ground layer. Power supply routes should be heavy copper fill planes to ensure the lowest possible inductance. The power pins of the module should have a via directly to the power plane as close to the pin as possible. Decoupling capacitors should have a via right next to the capacitor pin and this via should go directly down to the power plane – that is to say, the capacitor should not route to the power plane through a long trace. The ground side of the decoupling capacitor should have a via right next to the pad which goes directly down to the ground plane. Each decoupling capacitor should have its own via directly to the ground plane and directly to the power plane right next to the pad. The decoupling capacitors should be placed as close to the pin that it is filtering as possible.

9 Interferers

One of the biggest problems with RF receivers is poor performance due to interferers on the board radiating noise into the antenna or coupling into the RF traces going to input LNA. Care must be taken to make sure that there is no noisy circuitry placed anywhere near the antenna or the RF traces. All noise generating circuits should also be shielded so they do not radiate noise that is picked up by the antenna. Also, make sure that no traces route underneath the RF portion of the ATBTLC1000-MR110CA. Also, make sure that no traces route underneath any of the RF traces from the antenna to the ATBTLC1000-MR110CA input. This applies to all layers. Even if there is a ground plane on a layer between the RF route and another signal, the ground return current will flow on the ground plane and couple into the RF traces.

10 Reference Documentation and Support

10.1 Reference Documents

Atmel offers a set of collateral documentation to ease integration and device ramp.

The following list of documents available on Atmel web or integrated into development tools.

Title	Content
Datasheet	This document
ATBTLC1000 SOC Datasheet	Data sheet for the ATBTLC1000 SOC contained on this module.
ATBTLC1000 BluSDK: Hardware Design Guidelines	ATBLTC1000 hardware design guide with references for placement and routing, external RTC, restrictions on power states, type of information.
ATBTLC1000 BluSDK Release Package	This package contains the software development kit and all the necessary documentation including getting started guides for interacting with different hardware devices, device drivers, and API call references.

11 Certifications

11.1 Agency Compliance

The ATBTLC1000-MR110CA has been tested and certified to meet the compliance for the following agencies:

- Bluetooth 4.1
 - QD ID Controller (see declaration [D028678](#))
 - QD ID Host (see declaration [D028679](#))
- FCC
 - FCC ID: [2ADHKB TLC1000](#)
- CFR47 Part 15
- ETSI
 - EN 300 328
 - EN 300 400 Class 2
- ARIB
 - STD-T66
- TELEC

12 Reflow Profile Information

This chapter provides guidelines for reflow processes in getting the Atmel module soldered to the customer's design.

12.1 Storage Condition

12.1.1 Moisture Barrier Bag Before Opened

A moisture barrier bag must be stored in a temperature of less than 30°C with humidity under 85% RH.

The calculated shelf life for the dry-packed product shall be 12 months from the date the bag is sealed.

12.1.2 Moisture Barrier Bag Open

Humidity indicator cards must be blue, <30%.

12.2 Stencil Design

The recommended stencil is laser-cut, stainless-steel type with a thickness of 100µm to 130µm, and approximately a 1:1 ratio of stencil opening to pad dimension. To improve paste release, a positive taper with bottom opening 25µm larger than the top can be utilized. Local manufacturing experience may find other combinations of stencil thickness and aperture size to get good results.

12.3 Baking Conditions

This module is rated at MSL level 3. After the sealed bag is opened, no baking is required within 168 hours so long as the devices are held at ≤30°C/60% RH or stored at <10% RH.

The module will require baking before mounting if:

- The sealed bag has been open for >168 hours
- Humidity Indicator Card reads >10%
- SIPs need to be baked for 8 hours at 125°C

12.4 Soldering and Reflow Condition

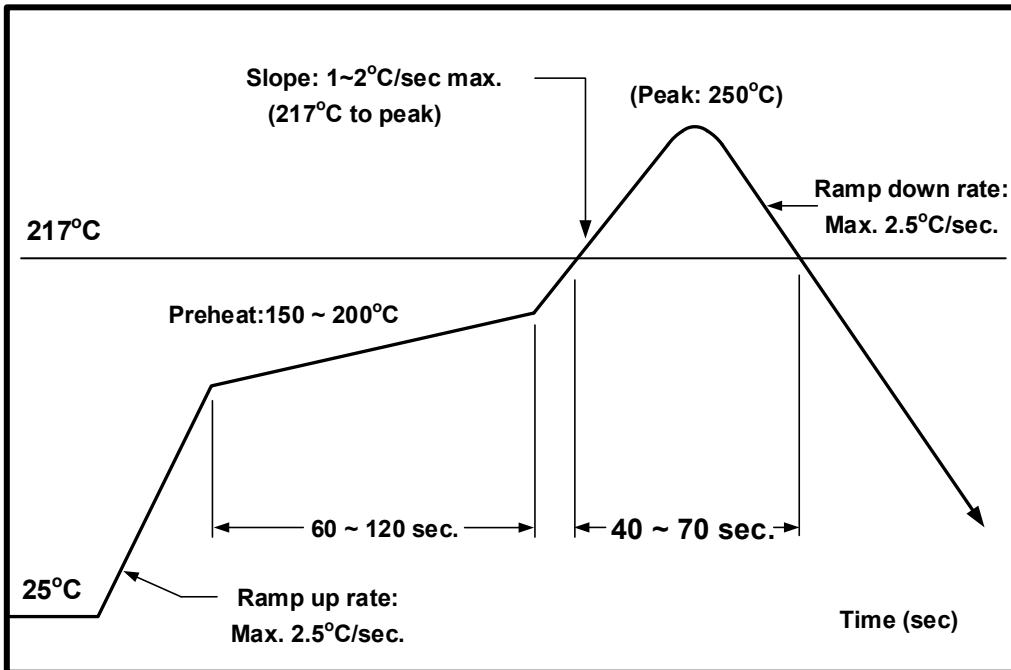
12.4.1 Reflow Oven

It is strongly recommended that a reflow oven equipped with more heating zones and Nitrogen atmosphere be used for lead-free assembly. Nitrogen atmosphere has shown to improve the wet-ability and reduce temperature gradient across the board. It can also enhance the appearance of the solder joints by reducing the effects of oxidation.

The following bullet items should also be observed in the reflow process:

- Some recommended pastes include NC-SMQ® 230 flux and Indalloy® 241 solder paste made up of 95.5 Sn/3.8 Ag/0.7 Cu or SENJU N705-GRN3360-K2-V Type 3, no clean paste.
- Allowable reflow soldering times: Three times based on the following reflow soldering profile (see [Figure 12-1](#)).
- Temperature profile: Reflow soldering shall be done according to the following temperature profile (see [Figure 12-1](#)).
- Peak temp: 250°C.

Figure 12-1. Solder Reflow Profile



12.5 Module Assembly Considerations

The ATBTLC1000-MR110CA modules are assembled with an EMI Shield to ensure compliance with EMI emission and immunity rules. The EMI shield is made of a tin-plated steel (SPTE) and is not hermetically sealed. Solutions like IPA and similar solvents can be used to clean the ATBTLC1000-MR110CA module. However, cleaning solutions, which contain acid, should never be used on the module.

The Atmel/Microchip ATBTLC1000-MR110CA modules are manufactured without any conformal coating applied. It is the customer's responsibility if a conformal coating is specified and or applied to the ATBTLC1000-MR110CA module.

13 Errata

Issue: The measured current for the device state cases listed in Table 6-1 will be higher than what is reported in the table.

This is because the Power number values in the SDK4.0 release have not been fully optimized to their final values.

A small sample measurement has been performed on 10 samples and they show the following results:

Measurement condition:

- 1-sec adverting interval
- 37 byte advertising payload
- Connectable beacon
- Advertising on three channels (37, 38, and 39)
- VBAT and VDDIO are set to 3.3V

SAM L21 has a measurement floor of 80nA which was compensated in the reported numbers (this number varies from board to board and needs to be compensated).

The Average advertising current: 11.3 μ A

The Average sleep current between beacons: 1.17 μ A

The average current for the 10 boards was (including 80nA floor):

Sample #	1	2	3	4	5	6	7	8	9	10
Average Current (μ A)	11.55	11.45	11.45	11.7	11.4	11.25	10.95	11.2	11.6	11.4

Workaround: Will be resolved in an SDK update.

For a complete listing of development support tools and documentation, visit <http://www.atmel.com/> or contact the nearest Atmel field representative.

14 Revision History

Doc Rev.	Date	Comments
42514E	8/2016	<ol style="list-style-type: none"> 1. Corrected module pad width in Table 2-1. 2. Revised Note 2 Vain in Absolute Max Power Ratings in Table 5-1. 3. Updated RTC pictures in Figure 5-3. 4. Replaced KHz with kHz. 5. Added Placement and cutout drawings in 0, and Figure 8-1. 6. Updated current values in Table 5-2. 7. Revised Module POD and Footprint in Figure 4-2 and Figure 4-3. 8. Revised VDDIO max voltage in Table 5-1. 9. Revised receive current in Table 6-1. 10. Added tolerance to freq dev in Table 6-3. 11. Revised receive performance numbers in Table 6-2. 12. Added section 12.5 for module assembly considerations. 13. Minor edits.
42514D	03/2016	<ol style="list-style-type: none"> 1. Corrected package table ground pad size in Table 2-1. 2. Updated module drawing in Figure 4-2. 3. Corrected Errata to refer to Table 6-1. 4. Revised reflow recurrence in Section 13.
42514C	12/2015	<ol style="list-style-type: none"> 1. Updated performance numbers. 2. Added UART Flow Control. 3. Added clearer diagrams. 4. Added Agency Certification section. 5. Corrected Package size value in Order information Chapter Table 1-1. 6. Updated Module Drawing figure in Section 4.3. 7. Revised Schematic content Chapter 7. 8. Added Reflow Profile Chapter 12. 9. Added Errata Chapter 13.
42514B	07/2015	Updated for B0 silicon
42514A	04/2015	Initial release